

7/Amend B
1. Sept 10
11/10

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

ROBERT H. HAVEMANN ET AL.

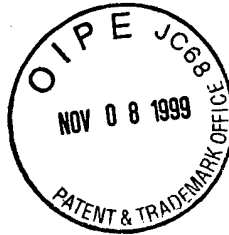
Serial No. 09/216,214 (TI-21570)

Filed December 18, 1998

For: ENHANCEMENT TO POLYSILICON GATE

Art Unit 2811

Examiner T. Tran



RECEIVED
NOV - 9 1999
TC 2800 MAIL ROOM

Assistant Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.115

In response to the Office action dated September 10, 1999, please amend the above identified application as follows:

In the claims:

Cancel claims 1 and 2 without prejudice.

Rewrite claim 8 as follows:

8. (Amended) A product by the method [of Claim 3] forming a transistor structure,

comprising the steps of:

(a) forming a dielectric over a semiconductor region;

(b) forming a patterned gate over said dielectric;

Sub D²
Gent